Amendments to the Claims

1. (*Previously Presented*)) A composite substrate comprising

a carrier composed of a carrier material,

a first layer composed of a first material, and

an intermediate layer composed of a second material being located between the carrier and the first layer, wherein the first material has a dilatation behavior being substantially the same as that of the carrier material, and having a dilatation mismatch with the second material, the intermediate layer having structures of second material for absorbing stress originating from the dilatation mismatch.

2. (*Original*) A composite substrate according to claim 1, wherein the intermediate layer has a thickness, and the structures extend through the thickness of the intermediate layer.

3. (*Original*) A composite substrate according to claim 1, wherein the structures further extend into the carrier.

4. (*Original*) A composite substrate according to claim 1, wherein the carrier material is the same as the first material.

5. (*Previously Presented*) A composite substrate according to claim 1, wherein the carrier material and the first material are semiconductors.

6. (*Previously Presented*) A composite substrate according to claim 1, wherein the second material is an electrically insulating material.

7. (*Previously Presented*) A composite substrate according to claim 1, the intermediate layer lying in a plane, wherein the dimensions of the structures in the plane of the intermediate layer are less than a centimeter.

8. (*Previously Presented*) A composite substrate according to claim 1, wherein the carrier lies in a plane and wherein the structures have a line-symmetric shape in a cross-section perpendicular to the plane of the carrier.

9. (*Previously Presented*) A composite substrate according to claim 1, wherein the carrier lies in a plane and wherein the structures have a circular, square, rectangular or rhombic shape in a cross-section parallel to the plane of the carrier.

10. (*Previously Presented*) A composite substrate according to claim 1, wherein the composite substrate is a silicon-on-insulator wafer.

Claims 11-20 (*Cancelled*)